

forming a photoresist film pattern on a semiconductor substrate
excluding a first region;

performing a first halo implant process twice on the first region of the
semiconductor substrate by using a tilt angle of about 45° and twist angles of
0° and 180°; and

performing a second halo implant process on the first region of the
semiconductor substrate by using a tilt angle of about 0°.

2. (Twice Amended) The method according to claim 1, wherein the first
halo implant process is performed with an energy of 20KeV and a dose of
 4.0×10^{12} ions/cm².

4. (Twice Amended) The method according to claim 1, wherein the
second halo implant process is performed only once at a tilt angle of about 0°.

5. (Twice Amended) The method according to claim 1, wherein the
second halo implant process is performed with an energy of 16KeV and a dose
of 4×10^{12} unit

8. (Twice Amended) A method for forming a junction in a semiconductor
device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

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impl.* performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively; and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°.
